

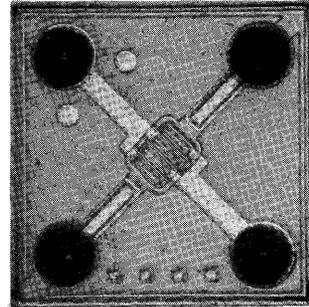
MMCF4338 (SILICON)

MMCF4339

FLIP-CHIP N-CHANNEL JUNCTION FIELD EFFECT TRANSISTORS

Flip-Chip — N-channel junction field effect transistor designed for low-level audio and general purpose applications.

- Drain and Source Interchangeable
- Excellent Performance as High-Impedance Input
- Low Pinch-Off Voltage Permits Use in Battery Driven Applications.



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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	50	Vdc
Drain-Gate Voltage	V_{DG}	50	Vdc
Gate-Source Voltage	V_{GS}	50	Vdc
Drain Current	I_D	50	mAdc
Operating Junction Temperature	T_J	+175	°C

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
Gate-Source Breakdown Voltage ($I_G = 10 \mu\text{A}_{dc}$, $V_{DS} = 0$)	$V_{(BR)GSS}$	50	—	Vdc
Gate Reverse Current ($V_{GS} = 30 \text{ Vdc}$, $V_{DS} = 0$)	I_{GSS}	—	1.0	nA _{dc}
Gate-Source Pinch-Off Voltage ($V_{DS} = 20 \text{ Vdc}$, $I_D = 1.0 \text{ nA}_{dc}$)	$V_{GS(off)}$	0.3 0.6	1.0 1.8	Vdc
Zero-Gate Voltage Drain Current ($V_{DS} = 15 \text{ Vdc}$, $V_{GS} = 0$)	I_{DSS}	0.2 0.5	0.6 1.5	mA _{dc}
Forward Transmittance ($V_{DS} = 15 \text{ Vdc}$, $V_{GS} = 0$, $f = 1.0 \text{ kHz}$)	$ Y_{fs} $	600 800	1800 2400	μmhos
Input Capacitance ($V_{DS} = 15 \text{ Vdc}$, $V_{GS} = 0$, $f = 1.0 \text{ MHz}$)	C_{iss}	—	7.0	pF
Reverse Transfer Capacitance ($V_{DS} = 15 \text{ Vdc}$, $V_{GS} = 0$, $f = 1.0 \text{ MHz}$)	C_{rss}	—	3.0	pF

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